

5DS33B

Switching Diode



Features

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- High Voltage General Purpose Diode

Item	Characteristics
Wafer size	5inch
Chip size	380*380um

Maximum Ratings @25degC

Item	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V _{RSM}	250	V
Repetitive Peak Reverse Voltage	V _{RRM}	250	V
Average Rectified Forward Current	I _{F (AV)}	200	mA
Repetitive Peak Forward Current	I _{FRM}	625	mA
Non-Repetitive Peak Forward Current @t=1us	I _{FSM}	9	A
Power Dissipation	P _D	400	mW
Junction Temperature	T _j	175	degC
Storage Temperature	T _{stg}	-65to+175	degC

Electrical Characteristics @25degC

Item	Symbol	Min	Max	Unit	Test Condition
Breakdown Voltage	BV	250		V	I _R =100uA
Forward Voltage	V _F		1.0	V	I _F =100mA
			1.25	V	I _F =200mA
Reverse Current	I _R		100	nA	V _R =200V
Junction Capacitance	C _T		5	pF	V _R =0V, f=1MHz
Reverse Recovery Time	t _{rr}		50	nsec	I _F =I _R =30mA R _L =100Ω

Probing Spec @25degC

Symbol	Min	Max	Unit	Test Condition
BV	260		V	I _R =100uA
V _{F1}		980	mV	I _F =100mA
V _{F2}		1.2	V	I _F =200mA
I _R		98	nA	V _R =200V
C _T		5	pF	V _R =0V, f=1MHz
t _{rr}		50	nsec	I _F =I _R =30mA, R _L =100Ω

Note Equivalent type : BAV21

SheetNo.

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